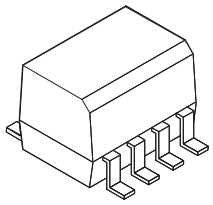
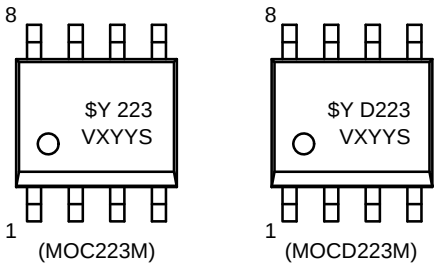




$Y	=	Logo
223/D223	=	Specific Device Code
V	=	DIN EN/IEC60747−5−5 Option
X	=	One−Digit Year Code
YY	=	Digit Work Week
S	=	Assembly Package Code

- These Devices are Pb−Free and Halogen Free

- Low Power Logic Circuits
- Interfacing and Coupling Systems of Different Potentials and Impedances
- Telecommunications Equipment
- Portable Electronics
- Solid State Relays

See detailed ordering and shipping information on page 7 of this data sheet.

Publication Order Number:
EN/IEC60747−5−5, 565 V Peak W

T_A = 25°C unless otherwise specified.

	ature	−40 to +125	°C
	ng Temperature	−40 to +100	
	rature	−40 to +125	
	nperature	260 for 10 s	
	ver Dissipation @ T_A = 25°C	240	mW
	5°C	2.94	mW/°C
	vard Current	60	mA
	− Peak (PW = 100 μs, 120 pps)	1.0	A
		6.0	V
	ipation @ T_A = 25°C	90	mW
	5°C	0.8	mW/°C
	ector Current	150	mA
	r Voltage	30	V
	Voltage, MOC223M	70	
	r Voltage	7	
P_D	Detector Power Dissipation @ T_A = 25°C	150	mW
	Derate Above 25°C	1.76	mW/°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

T_A = 25°C unless otherwise specified.

V_F	Input Forward Voltage	I_F = 1.0 mA	−	1.08	1.3	V
I_R	Reverse Leakage Current	V_R = 6.0 V	−	0.001	100	μA
C_{IN}	Input Capacitance		−	18	−	pF
I_{CEO1}	Collector−Emitter Dark Current	V_{CE} = 5.0 V, T_A = 25°C	−	1.0	50	nA
I_{CEO2}		V_{CE} = 5.0 V, T_A = 100°C	−	1.0	−	μA
BV_{CEO}	Collector−Emitter Breakdown Voltage	I_C = 100 μA	30	100	−	V
BV_{CBO}	Collector−Base Breakdown Voltage	I_C = 100 μA	70	120	−	
BV_{ECO}	Emitter−Collector Breakdown Voltage	I_E = 100 μA	7	10	−	
C_{CE}	Collector−Emitter Capacitance	f = 1.0 MHz, V_{CE} = 0	−	5.5	−	pF

CTR	Current Transfer Ratio	I

T_A = 25°C unless otherwise specified. (continued)

V_{ISO}	Input−Output Isolation Voltage	t = 1 min	2500	−	−	VAC_{RMS}
C_{ISO}	Isolation Capacitance	$V_{I−O}$ = 0, f = 1 MHz	−	0.2	−	pF
R_{ISO}	Isolation Resistance	$V_{I−O}$ = ±500 V_{DC}, T_A = 25°C	10^{11}	−	−	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1.8

1.7

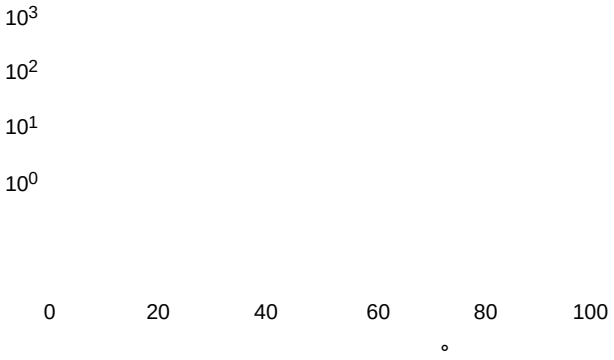
1.6

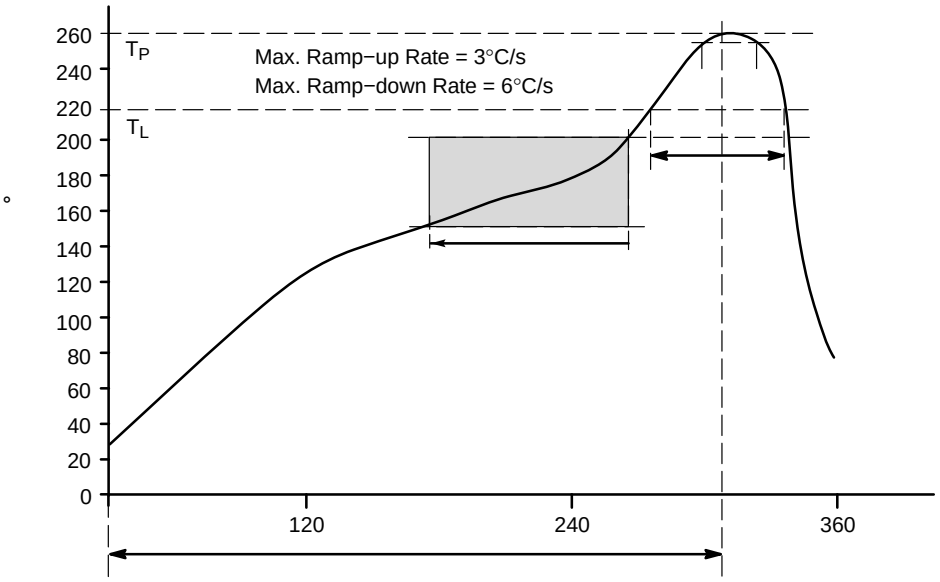
1.5

1.0

1 10 100

0


10^3
10^2
10^1
10^0
0
20
40
60
80
100
°


260
240
220
200
180
160
140
120
100
80
60
40
20
0
°
T_P
T_L
Max. Ramp−up Rate = 3°C/s
Max. Ramp−down Rate = 6°C/s
120
240
360

		†
MOC223M	Small Outline 8−Pin	50 Units / Tube
MOC223R2M	Small Outline 8−Pin	2500 Units / Tape and Reel
MOC223VM	Small Outline 8−Pin, DIN EN/IEC60747−5−5 Option	50 Units / Tube
MOC223R2VM	Small Outline 8−Pin, DIN EN/IEC60747−5−5 Option	2500 Units / Tape and Reel
MOCD223M	Small Outline 8−Pin	50 Units / Tube
MOCD223R2M	Small Outline 8−Pin	2500 Units / Tape and Reel
MOCD223VM	Small Outline 8−Pin, DIN EN/IEC60747−5−5 Option	50 Units / Tube
MOCD223R2VM	Small Outline 8−Pin, DIN EN/IEC60747−5−5 Option	2500 Units / Tape and Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ISSUE O

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